Terahertz radiation by ultrafast spontaneous polarization modulation in multiferroic $BiFeO_3$ thin lm s

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Terahertz (THz) radiation has been observed from multiferroic BiFeO₃ thin $\ln s$ via ultrafast modulation of spontaneous polarization upon carrier excitation with illumination of fem to second laser pulses. The radiated THz pulses from BiFeO₃ thin $\ln s$ were clarified to directly reject the spontaneous polarization state, giving rise to a memory elect in a unique style and enabling THz radiation even at zero-bias electric eld. On the basis of our indings, we demonstrate potential approaches to ferroelectric nonvolatile random access memory with nondestructive readability and ferroelectric dom ain in aging microscopy using THz radiation as a sensitive probe.

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Ferroelectric oxides o er a wide range of functionalities dem onstrating their potential for various electronic and photonic applications such as capacitors for data storage devices, piezoelectric actuators, and nonlinear optical devices for frequency conversion of laser lights [1]. Am ong them, BFeO3 with a perovskite structure has recently attracted much attention for the presence of multiferroism at room tem perature with simultaneous ferroelectricity and antiferrom agnetism, as well as for the extrem ely large spontaneous polarization P_s observed in thin lm form [2, 3]. BiFeO 3 is a charge-transfer insulator exhibiting an energy gap of about 2.5 eV [4], which is quite sm all in contrast with the ordinary ferroelectrics whose energy gap generally lies in the ultraviolet region. Such distinct feature allows carrier excitation in B FeO 3 with commercially available fem to second laser pulses, and hence, enables us to develop ferroelectric ultrafast optoelectronic devices as widely dem onstrated in sem iconductors.

In this Letter, we report a novel terahertz (THz) radiation characteristic ofm ultiferroic B iFeO₃ thin In s via exciting charge carriers upon illum ination of fem to second laser pulses. B ased on the bias electric eld dependence of the THz amplitude, we show that the radiated THz pulse directly re ects the P_s state indicating that THz radiation results from the ultrafast modulation of P_s of the B iFeO₃ thin In s. This phenom enon can be applied universally to other ferroelectrics and provides new approaches to various potential applications such as readout in nonvolatile random access m em ories and ferroelectric dom ain im aging system s.

U ltrafast laserpulses enable us to produce a wide range of unique phenom ena in condensed matter. THz radiation via exciting charge carriers upon illum ination of ultrafast laser pulses is a typical example, which provides considerable interest owing to a variety of applications such as imaging for biom edical diagnosis and security, tim e-dom ain spectroscopy for material characterization, and a tool to evaluate the ultrafast dynamics of photo excited charge carriers [5, 6]. Intensive studies have therefore been carried out on THz radiation from photoconductive switches fabricated on various materials. The mechanism of THz radiation from photoconductive switch is dom inated by the dynam icalm otion of the free carriers created by laser illum ination, in which the transient current surge developed within subpicosecond time scale upon carrier excitation gives rise to electrom agnetic radiation at THz frequencies. Through this approach, voltage-biased sem iconductors have shown the best radiation e ciency am ong others dem onstrating their potential as a general THz radiation source [6]. On the other hand, transition m etaloxides with perovskite structures have presented peculiar TH z radiation characteristics originating from their strong electron correlations as exemplied by the cases of high-transition-temperature cuprate superconductors [7, 8, 9] and colossal magneto resistive m anganites [10, 11, 12, 13]. The present work on multiferroic BiFeO₃ thin Im s provides an alternate route to THz radiation based on this photoconductive approach.

200 nm -thick BiFeO₃ thin Im s with (001) orientation were grown on (LaA D₃)_{0:3} (Sr₂A I aO ₆)_{0:7} (001) substrates, abbreviated as LSAT, by pulsed laser deposition technique with a K rF excineer laser at a growth condition of 800 C for substrate temperature and 60 Pa for oxygen pressure. The ferroelectricity and the antiferrom agnetism of the obtained BiFeO₃ thin Im s at room temperature were con Im ed by a ferroelectric tester and superconducting quantum interface device magnetom eter, respectively.

A dipole-type photoconductive switch consisting of a pair of Au electrodes was fabricated on the lm by a conventional photolithography and sputtering m ethod. The Au electrode of the photoconductive switch consists of a pair of 30 m-wide strip lines separated by 20 m with



FIG.1: (color) (a) Schematic of terahertz (THz) radiation from a BiFeO₃ photoconductive switch. (b) Time-domain waveform of the THz pulse radiated from a BiFeO₃ photoconductive switch measured at zero-bias electric eld after applying a bias electric eld $E_{\rm bias}$ of 200 kV/cm. The dashed line represents the zero-level line shown for clarity. (c) Fourier transform ed am plitude spectrum of the THz waveforms in (b).

a dipole gap of 10 m.

In Fig. 1(a), we present the schematic illustration of THz radiation from a photoconductive switch fabricated on a BiFeO₃ thin Im. Generation of a single-cycle THz pulse propagating into free space was achieved by carrier excitation upon illumination of fem to second laser pulses with a center wavelength of 400 nm. We used the second harm onic of a mode-locked T is apphire laser with a repetition rate of 82 MHz, of 800 nm, and pulse duration of 100 fs, which was generated through a BaB_2O_4 crystal. The laser power at of 400 nm was xed at 5.5 mW and focused to a spot diam eter of 20 m. We employed a conventional photoconductive sam pling technique using a bow-tie-type low-tem perature-grown G aAs photoconductive switch as a detector [6]. All measurements were perform ed at room tem perature.

Figure 1(b) shows a typical example of two timedomain THz waveforms radiated from the BiFeO₃ photoconductive switch in the absence of an external bias electric eld E_{bias} , measured after once applying E_{bias} of

200 kV/cm. The two TH z waveform s m easured under the same condition but with di erent initial treatment, are nearly identical, both consisting of a single-cycle pulse centered at 0 ps with a pulse width of about 0.84 ps, except that they have a reversed phase by with one another. Thus, they show an identical Fourier transform ed amplitude spectrum exhibiting a frequency component extending up to 1 TH z Fig. 1 (c)]. These features where THz radiation is observed even at zero-bias electric eld and its phase depends on the polarity of the initially applied $E_{\rm bias}$, provide a ferroelectric peculiarity that the history of the applied $E_{\rm bias}$ is mem orized and the rem – nant polarization of B FeO₃ substitutes for $E_{\rm bias}$, which is essential for THz radiation. This is in contrast to the case of photoconductive switches fabricated on nonferroelectric materials, where it requires constant application of $E_{\rm bias}$ to radiate a THz pulse [6].

THz radiation can also be achieved from transparent noncentrosymm etric materials through the second-order nonlinear optical e ect when they satisfy a severe phasem atching condition under the incidence of high-intensity laser pulses [6]. However, this common e ect observed in ferroelectrics does not contribute to the THz radiation presented here. We examined the response of BiFeO $_3$ thin Insto the illumination of laser pulses at of 800 nm, which show negligible absorption in BiFeO₃ [4]. Despite the high laser power of 180 mW illum inated onto the lm (this is about twenty times larger than the case at of 400 nm), THz radiation was not observed in this situation, indicating that THz radiation presented in Fig 1(b) is de nitely triggered by the photoexcited charge carriers and not by the nonlinear optical e ect, or the optically induced polarization transient as reported in ferroelectric LiN bO $_3$ [14] and LiT aO $_3$ [15].

Further showing that THz radiation re ects the P_s state of the BiFeO₃ thin lm, we measured the main peak amplitude of the THz pulse E_{THz} as a function of E_{bias} Fig. 2(a)]. In the photoconductive switches reported so far [6], which are all nonferroelectric, E_{THZ} generally has linear relationship with the applied E bias reversing its phase by when the polarity of E_{bias} is changed, without showing any hysteresis. However, in the case of BiFeO₃, we observed a clear hysteresis loop [Fig. 2(a)], which looks fam iliar with the common electric polarization hysteresis loop observed in ferroelectrics except for the slight tilted shape where the intensity of E_{THz} is suppressed at high E_{bias}. W e explain such hysteresis loop by considering the macroscopic electric eld biased to a pair of electrodes in typical ferroelectrics [Fig. 2(b)]. The effective m acroscopic electric eld E induced to a pair of electrodes is ideally expressed by $E_e = E_{polar} = E_{bias}$, where E_{polar} represents the electric eld derived from electric polarization (= P / 0; P: electric polarization and 0: electric constant). Due to the screening of E polar by E_{bias} , E_{e} is suppressed at high E_{bias} and shows a tilted hysteresis loop in analogy with the E_{THz} loop observed in Fig. 2(a). These features show the direct relationship of THz radiation with Ps, which emerges as a result of ultrafast Ps modulation introduced by the mobile photoexcited charge carriers. We assume that the ferroelectric ordering is not disarranged upon photoexcitation here because only a sm all am ount of photons is injected into the lm compared to the total number of the unit cell covered by the laser spot, i.e., the number



FIG.2: (color) E lectric polarization of B iFeO₃ thin lm probing with terahertz (THz) radiation. (a) The main peak am – plitude of the radiated THz pulse E_{THz} as a function of the applied bias electric eld. The measurement was performed by xing the laser spot onto the dipole gap. The arrows indicate the sequential directions. (b) An ideal model of the macroscopic electric eld induced to a pair of electrodes in typical ferroelectrics for understanding the tilted hysteresis loop in (a). E_e , E_{polar} , and E_{bias} represents the electric electric eld induced between the electrodes, electric eld derived by electric polarization, and applied bias electric eld, respectively. E_e is expressed by E_{polar} E_{bias} .

of injected photons per cubic centim eter is considered to be of the order of 10^{17} per pulse, whereas the number of the perovskite unit cells per cubic centim eter extends up to the order of 10^{22} .

Such characteristics open a way to a variety of applications using THz radiation as a sensitive probe. The hysteretic feature dem onstrates the potential of ferroelectric photoconductive devices to act as nonvolatile random access m em ories w here the w riting process w ill be perform ed by the application of E_{bias} , and the reading by detecting THz radiation. This is accomplished by laser illum ination and the 0", 1" inform ation is determ ined by the signs of E_{THZ} , whether positive or negative. To explicit the switching operation, the tem poral change of E_{THz} with varying E_{bias} is shown in Fig. 3(a). The application of positive $E_{\rm bias}$ of + 200 kV /cm $\mbox{Fig. 3(b)}\mbox{writes}$ down an information which is sustained even after the rem oval of E bias. TH z radiation is indeed detected only when the laser is illum inated onto the lm. In turn, the application of an opposite E_{bias} of 200 kV/cm erases the previous information and writes down a new information to the lm. We con med that the written inform ation was sustained for more than two weeks in the absence of E_{bias}, and also that 12 hours of continuous illum ination of laser pulses at zero-bias electric eld did not give rise to any suppression of E_{THz} nor a change of its phase. Since the \on" and \o " operation of laser



FIG. 3: Switching operation of BiFeO₃ photoconductive switch as a function of time probing with terahertz (THz) radiation. Temporal change of (a) THz amplitude E_{THz} and (b) the applied bias electric eld $E_{\rm bias}$. The dashed line represents the zero-level line shown for clarity.



FIG. 4: (color) V isualization of 180 ferroelectric domain structure of the B iFeO₃ thin lm probing with terahertz amplitude E_{THz} . D om ain structure after the application of bias electric eld $E_{\rm bias}$ of (a) + 200 kV/cm and (b) 200 kV/cm carried out with simultaneous laser illumination, and domain structure after the application of $E_{\rm bias}$ of (c) + 200 kV/cm and (d) 200 kV/cm carried out without laser illumination. The geometry of the dipole-type Au electrodes is also shown by the yellow line in the respective images. Opposite 180 ferroelectric domains are distinguished by the blue and red colors based on the sign of E_{THz} . The images showed no evolution with time as we repeated the scans of the same area for several days.

illum ination does not induce a change of the P_s state, this process can be regarded as a nondestructive readout. Note that the rather high $E_{\rm bias}$ applied here can be reduced down to at least 50 or 60 kV/cm assuming from the coercive eld estimated from Fig.2(a).

W ith the THz radiation exhibiting direct relationship

with Ps, scanning of the two-dimensional distribution of $E_{T\,H\,z}$ allow sus to visualize the ferroelectric dom ain structures by distinguishing the orientation of the 180 domains from the signs of E_{THz} . For demonstration, we applied this imaging technique to two di erent types of ferroelectric dom ain structures, which were realized by changing the poling conditions. In Fig. 4, we show four dom ain in ages of a section of the BiFeO₃ thin lm at zero-bias electric eld after the application of 200 kV/cm carried out with [Figs. 4(a) and 4(b)] and without Figs. 4(c) and 4(d)] simultaneous laser illum ination. The initial poling treatment of αE_{bias} of 200 kV/cm with simultaneous laser illum ination" is perform ed by once scanning the objective area at 200 kV /cm. This treatment was also carried out prior to the m easurement in Figs. 4(c) and 4(d). Thus, the former state before the poling treatment of Fig. 4(c) [Fig. 4(d)] corresponds to the image shown in Fig. 4(b) [Fig. 4(a)]. D om ains with opposite polarization states appear as blue and red areas depending on the sign of E $_{T\,H\,z}$. By com paring the images of each single pairs between Figs. 4 (a) and 4 (b), as well as Figs. 4 (c) and 4 (d)], one can see that only the domains between the electrodes has changed their states by the application of opposite E_{bias} , while the other areas are independent of E bias and rem ain unchanged. The di erent poling treatment, whether Ebias was applied with or without laser illum ination, gave rise to an interesting feature as dem onstrated by the com parison of the pair of Figs. 4 (a) and 4 (b) by the pair of Figs. 4 (c) and 4 (d). In Figs. 4 (a) and 4 (b), the entire dom ains between the electrodes have managed to reverse their phase by . Contrary, in Figs. 4(c) and 4(d), only the area near the dipole gap has reversed its dom ains where maximum electric eld is applied due to geometric e ect, while the other area between the two strip lines has not, realizing the coexistence of two opposite 180 domains aligned side by side between the electrodes. The origin of the two di erent states can simply be understood by the term \photoassisted P_s switching" previously reported in BaTiO₃ [16] and Pb (Zr,Ti)O₃ [17] thin lm s where the combination of ultraviolet light exposure with applying E bias showed superior switching ability than the application of E bias alone. It is also notew orthy here that we observed THz radiation even in the areas apart from the electrodes where the domains had not been arti cially aligned. However, the intensity of E_{THz} in these areas is considerably weak presum ably because the domains are not aligned neatly as in the areas between the electrodes. These in aging results indicate that THz radiation occurs from individual ferroelectric dom ains and the intensity of E_{THZ} is determined by the average of the electric dipole m om ents of which the laser spot covers. Since the spatial resolution of this in aging technique is limited by the diameter of the focused laser spot, we assume that a more detailed dom ain structure can be observed by focusing the laser spot down to a submicrom – eter scale. This guarantees the potential of the present technique to compete evenly with the other fascinating ferroelectric dom ain in aging tools such as atom ic force microscopy [18] and x-ray microdi raction [9].

In conclusion, we have demonstrated a novel THz radiation functionality of a multiferroic BiFeO₃ thin Im triggered via ultrafast modulation of P_s upon carrier excitation by the illum ination of fem to second laser pulses. By utilizing the hysteretic THz radiation characteristic where E_{THz} directly relect the P_s state, we have also presented potential approaches to nondestructive readout in nonvolatile ferroelectric memory and 180 ferroelectric domain imaging system. Since BiFeO₃ belongs to a class of multiferroics, measurement under magnetic

eld is promising, for it may give rise to an additional degree of freedom in the THz radiation feature also providing an additional functionality in device designing.

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